捷多邦,专业PCB打样工厂,24小时加急出货 查询BCR2PM-12RE供应商 **KENES** BCR2PM-12RE Triac Low Power Use REJ03G1468-0100 Rev.1.00 Jul 31, 2006 **Features** • $I_{T(RMS)}$: 2 A Insulated Type V_{DRM}: 600 V Planar Passivation Type I_{RGTI}, I_{RGT} : 10 mA The product guaranteed maximum junction temperature 150°C. Outline RENESAS Package code: PRSS0003AA-B (Package name: TO-220F(2)) T₁ Terminal 2. T₂ Terminal 3. Gate Terminal 2 3 WWW.DZSC.COM

Applications

Electric rice cooker, electric pot, and controller for other heater

Precautions on Usage

When the BCR2PM-12RE is used, do not attach the heat radiating fin.

Maximum Ratings

Parameter	Symbol	Symbol Voltage class			
Repetitive peak off-state voltage ^{Note1}	V _{DRM}	600	V		
Non-repetitive peak off-state voltage ^{Note1}	V _{DSM}	720	V		



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Parameter	Symbol	Ratings	Unit	Conditions	
RMS on-state current	I _{T (RMS)}	2	A	Commercial frequency, sine full wave 360° conduction	
Surge on-state current	I _{TSM}	10	A	60Hz sinewave 1 full cycle, peak value, non-repetitive	
I ² t for fusing	l ² t	0.41	A ² s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current	
Peak gate power dissipation	P _{GM}	1	W		
Average gate power dissipation	P _{G (AV)}	0.1	W		
Peak gate voltage	V _{GM}	6	V		
Peak gate current	I _{GM}	1	A		
Junction temperature	Tj	- 40 to +150	°C		
Storage temperature	Tstg	- 40 to +150	°C		
Mass	—	2.0	g	Typical value	

Notes: 1. Gate open.

Electrical Characteristics

Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions	
Repetitive peak off-state cur	rent	I _{DRM}			1.0	mA	$Tj = 150^{\circ}C, V_{DRM}$ applied	
On-state voltage		V _{TM}		_	1.6	V	$Tj = 25^{\circ}C, I_{TM} = 1.5 A,$	
							Instantaneous measurement	
Gate trigger voltage ^{Note2}	II	V _{RGTI}			2.0	V	$Tj=25^{\circ}C,\ V_{D}=6\ V,\ R_{L}=6\ \Omega,$	
	III	V _{RGTIII}	—	—	2.0	V	$R_{G} = 330 \Omega$	
Gate trigger current ^{Note2}	II	I _{RGTI}			10	mA	$ \begin{array}{l} Tj=25^{\circ}C, \ V_{D}=6 \ V, \ R_{L}=6 \ \Omega, \\ R_{G}=330 \ \Omega \end{array} $	
	III	I _{RGTIII}	_	_	10	mA		
Gate non-trigger voltage		V_{GD}	0.1	_	_	V	$Tj = 150^{\circ}C, V_D = 1/2 V_{DRM}$	
Thermal resistance		R _{th (j-a)}	_	_	45	°C/W	Junction to ambient,	
							Natural convection	

Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

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Performance Curves





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Package Dimensions



Order Code

Standard packing	Quantity	Standard order code	Standard order code example
Vinyl sack	100	Type name	BCR2PM-12RE
Plastic Magazine (Tube)	50	Type name – Lead forming code	BCR2PM-12RE-A8
	Vinyl sack	Vinyl sack 100	Vinyl sack 100 Type name

Note : Please confirm the specification about the shipping in detail.

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